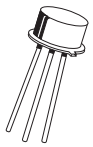
BSX62
BSX63

NPN SILICON TRANSISTOR



TO-39 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR BSX62, BSX63 types are NPN Silicon Transistors designed for general purpose applications where high collector current is required.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C)	**SYMBOL**	**BSX62**	**BSX63**	**UNITS**
Collector-Base Voltage	V_{CBO}	60	80	V
Collector-Emitter Voltage	V_{CEO}	40	60	V
Emitter-Base Voltage	V_{EBO}	5.0		V
Collector Current	I_C	3.0		A
Power Dissipation	P_D	5.0		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		°C
Thermal Resistance	Θ_{JC}	35		°C/W

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=40V (BSX62)			100	nA
I_{CBO}	V_{CB}=40V, T_C=150°C (BSX62)			100	µA
I_{CBO}	V_{CB}=60V (BSX63)			100	nA
I_{CBO}	V_{CB}=60V, T_C=150°C (BSX63)			100	µA
I_{EBO}	V_{EB}=5.0V			100	nA
$V_{CE(SAT)}$	I_C=1.0A, I_B=100mA			0.7	V
$V_{CE(SAT)}$	I_C=2.0A, I_B=200mA			0.8	V
$V_{BE(SAT)}$	I_C=1.0A, I_B=100mA			1.2	V
$V_{BE(SAT)}$	I_C=2.0A, I_B=200mA			1.3	V
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=100mA			1.0	V
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=1.0A			1.2	V
$V_{BE(ON)}$	V_{CE}=5.0V, I_C=2.0A			1.3	V
h_{FE}	V_{CE}=1.0V, I_C=1.0A (BSX62, 63-10)	63		160	
h_{FE}	V_{CE}=1.0V, I_C=1.0A (BSX62, 63-16)	100		250	
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz			70	pF
f_T	V_{CE}=10V, I_C=200mA, f=100MHz	30			MHz
t_{on}	I_C=1.0A, I_{B1}=I_{B2}=50mA			300	ns
t_{off}	I_C=1.0A, I_{B1}=I_{B2}=50mA		4.0		µs

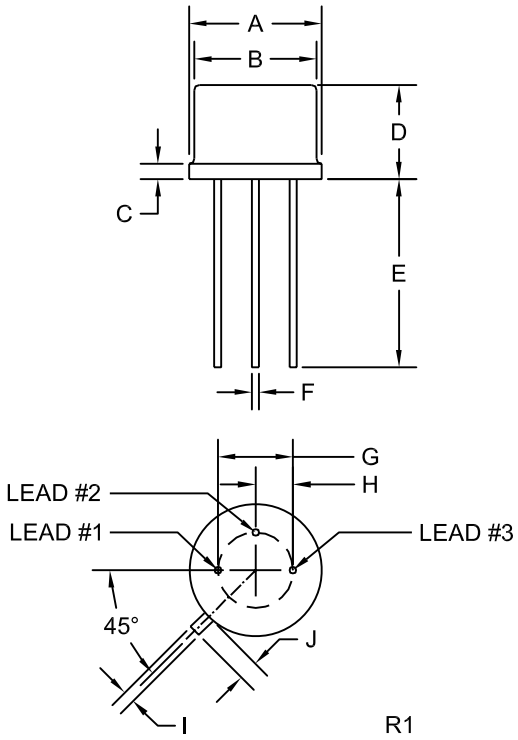
R0 (2-April 2008)

Central™
Semiconductor Corp.

BSX62
BSX63

NPN SILICON TRANSISTOR

TO-39 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:
1) EMITTER
2) BASE
3) COLLECTOR (case)

MARKING: FULL PART NUMBER

R0 (2-April 2008)